



# 《风光欣》技术资料

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## 2SA812

## TRANSISTOR (PNP)

### FEATURES

Power dissipation

PCM : 0.2W (Tamb=25 )

Collector current

ICM:-0.1A

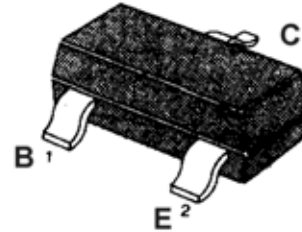
Collector-base Voltage

V(BR)CBO : -60V

Operating and storage junction temperature range

TJ,Tstg : -55 to+150

SOT-23



### ELECTRICAL CHARACTERISTICS (TA=25 )

Parameter	Symbol	Test conditons	MIN	Typ	MAX	UNIT
Collector -base breakdown voltage	V(BR)CBO	IC= -100 μ A,IE=0	-60			V
Collector-emitter breakdown Voltage	V(BR)CEO	IC= -10mA,IB=0	-50			V
Emitter-basebreakdown voltage	V(BR)EBO	IE= -100 μ A,IB=0	-5			V
Collector cut-off current	ICBO	VCB= -60V,IE=0			-0.1	μ A
Emitter cut-off current	IEBO	VEB= -5V,IC=0			-0.1	μ A
DC current gain	HFE	VCE= -6V,IC= -1mA	90	200	600	
Collector-emitter saturation voltage	VCEsat	IC= -100mA,IB= -5mA		-0.18	-0.3	V
Base-emitter saturation voltage	VBEsat	IC= -100mA,IB= -5mA			-1	V
Base-emitter voltage	VBEF	VCE= -6V,IE= -10mA	-0.55		-0.65	V
Transition frequency	fT	VCE= -6V,IC= -10mA		180		MHz

### CLASSIFICATON OF hFE

RANK	M4	M5	M6	M7
RANGE	90-180	135-270	200-400	300-600